

描述 / Descriptions

SOP-8 塑封封装双 N 沟道 MOS 场效应管。

Double N-CHANNEL MOSFET in a SOP-8 Plastic Package.

特征 / Features

$V_{DS}(V)=30V$ $I_D=16.5A$

$R_{DS(ON)}@10V<7m\Omega$ (Typ. 6.3mR)

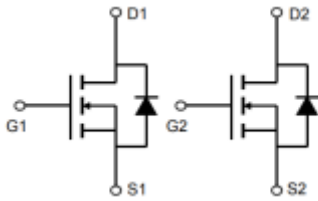
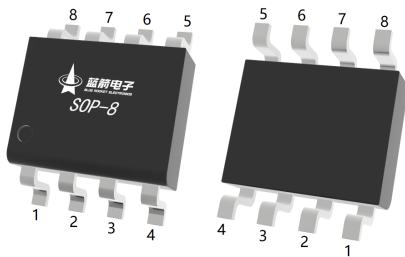
$R_{DS(ON)}@4.5V<12m\Omega$ (Typ. 9.5mR)

无卤产品。Halogen-free Product.

用途 / Applications

用于 MB/NB/UMPC/VGA 的高频负载点同步降压转换器,联网 DC-DC 电力系统,负荷开关。

High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA,
Networking DC-DC Power System,Load Switch.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN 1 : S1 PIN 2 : G1 PIN 3 : S2 PIN 4 : G2

PIN 5 : D2 PIN 6 : D2 PIN 7 : D1 PIN 8 : D1

印章代码 / Marking

见印章说明。

See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	16.5	A
Pulsed Drain Current	I_{DM}	63	A
Power Dissipation	P_D	3.2	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C
Maximum Junction-to-Ambient	$R_{\theta JA}(\text{Steady-State})$	39	°C/W

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	30	35		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V$ $V_{GS}=0V$			1	μA
Gate-Body leakage current	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.0	1.7	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=20A$		6.3	7	m Ω
		$V_{GS}=4.5V$ $I_D=10A$		9.5	12	m Ω
Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1.0A$			1.2	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		1170		pF
Output Capacitance	C_{oss}			110		pF
Reverse Transfer Capacitance	C_{rss}			100		pF
Gate resistance	R_g	$V_{DS}=0V$ $V_{GS}=0V$ $f=1.0MHz$		3.7		Ω
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$ $V_{DS}=15V$ $I_D=20A$		40		nC
Total Gate Charge	$Q_{g(4.5V)}$			22		nC
Gate-Source Charge	Q_{gs}			11		nC
Gate-Drain Charge	Q_{gd}			5		nC

电性能参数 / Electrical Characteristics(Ta=25℃)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=15\text{ V}$ $V_{GS}=10\text{ V}$ $R_L=0.75\Omega$ $R_{GEN}=3\Omega$		11		ns
Turn-On Rise Time	t_r			14		ns
Turn-Off Delay Time	$t_{d(off)}$			38		ns
Turn-Off Fall Time	t_f			10		ns

电参数曲线图 / Electrical Characteristic Curve

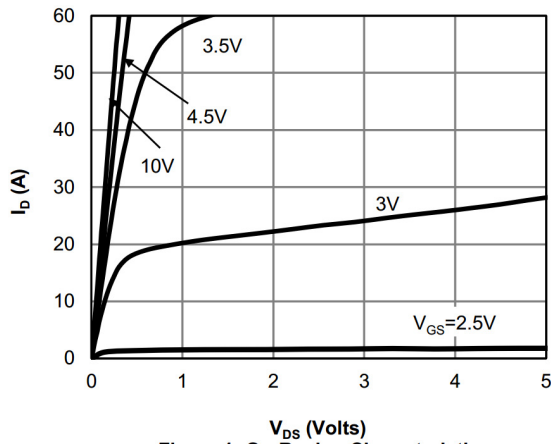


Figure 1: On-Region Characteristics

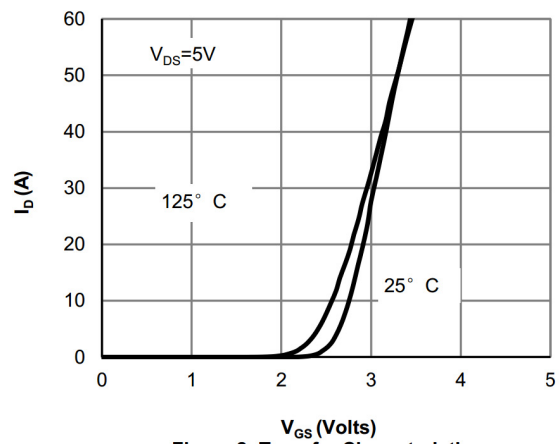


Figure 2: Transfer Characteristics

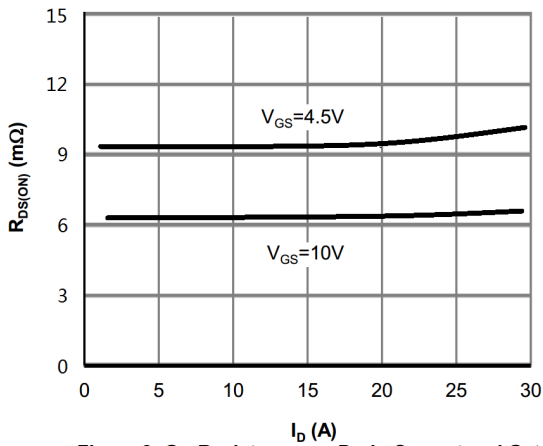


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

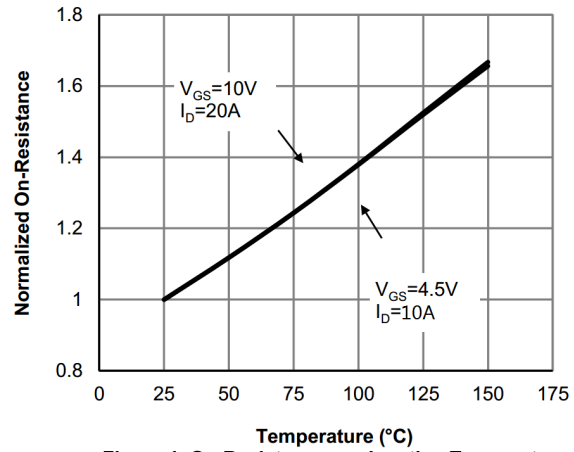


Figure 4: On-Resistance vs. Junction Temperature

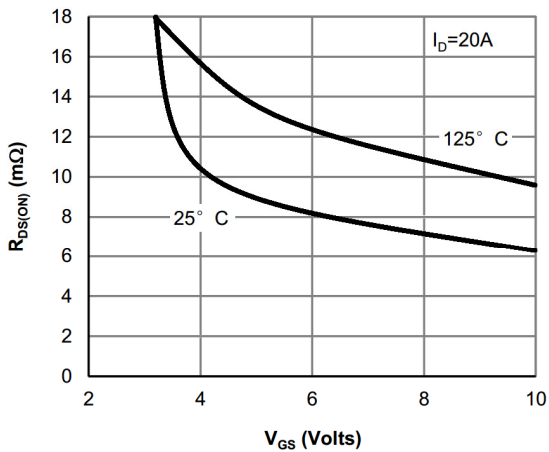


Figure 5: On-Resistance vs. Gate-Source Voltage

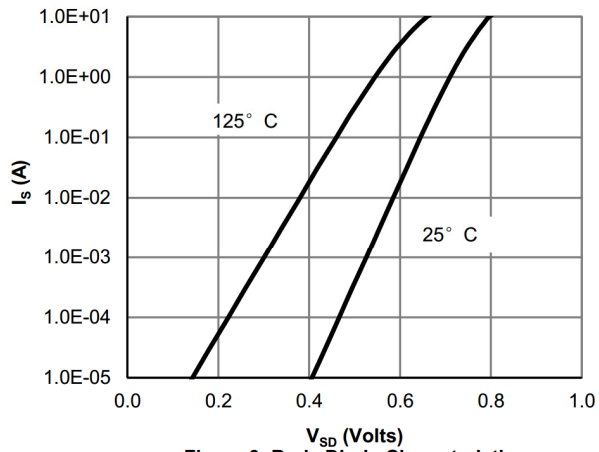
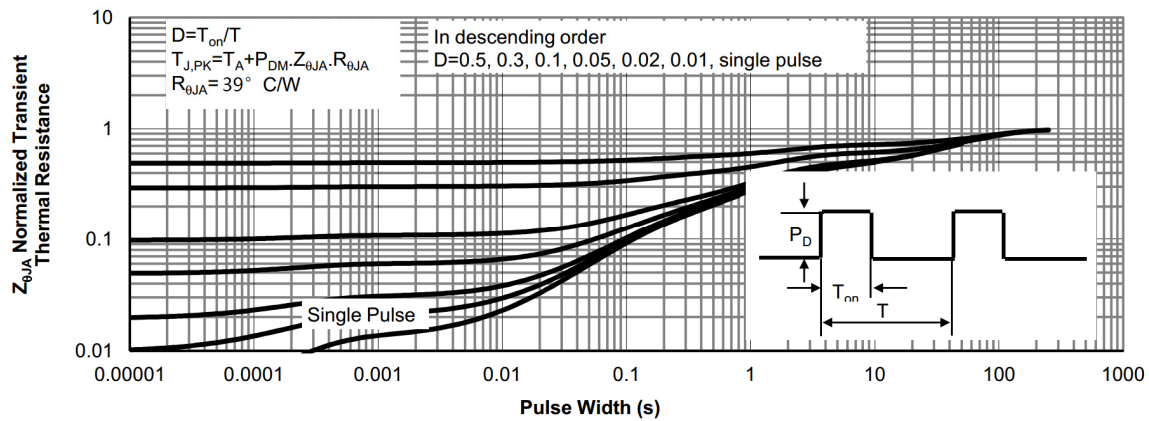
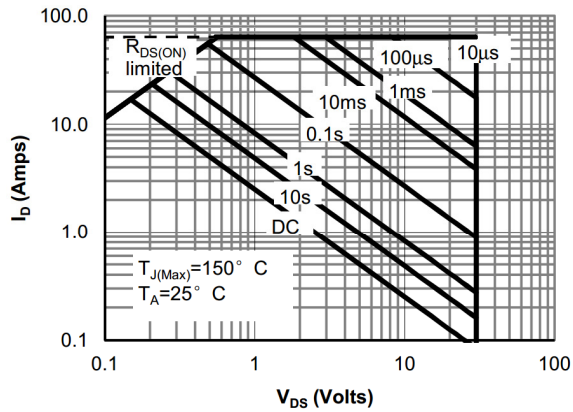
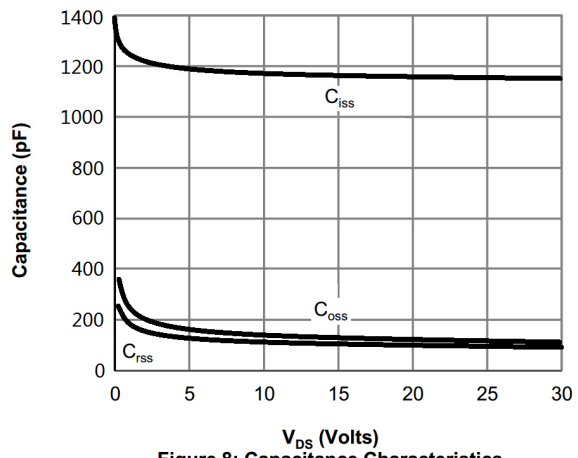
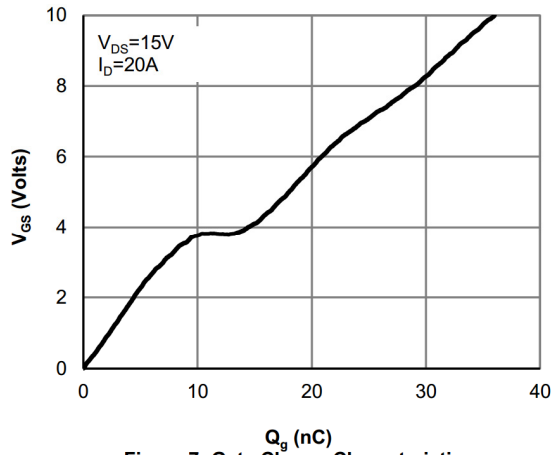


Figure 6: Body-Diode Characteristics

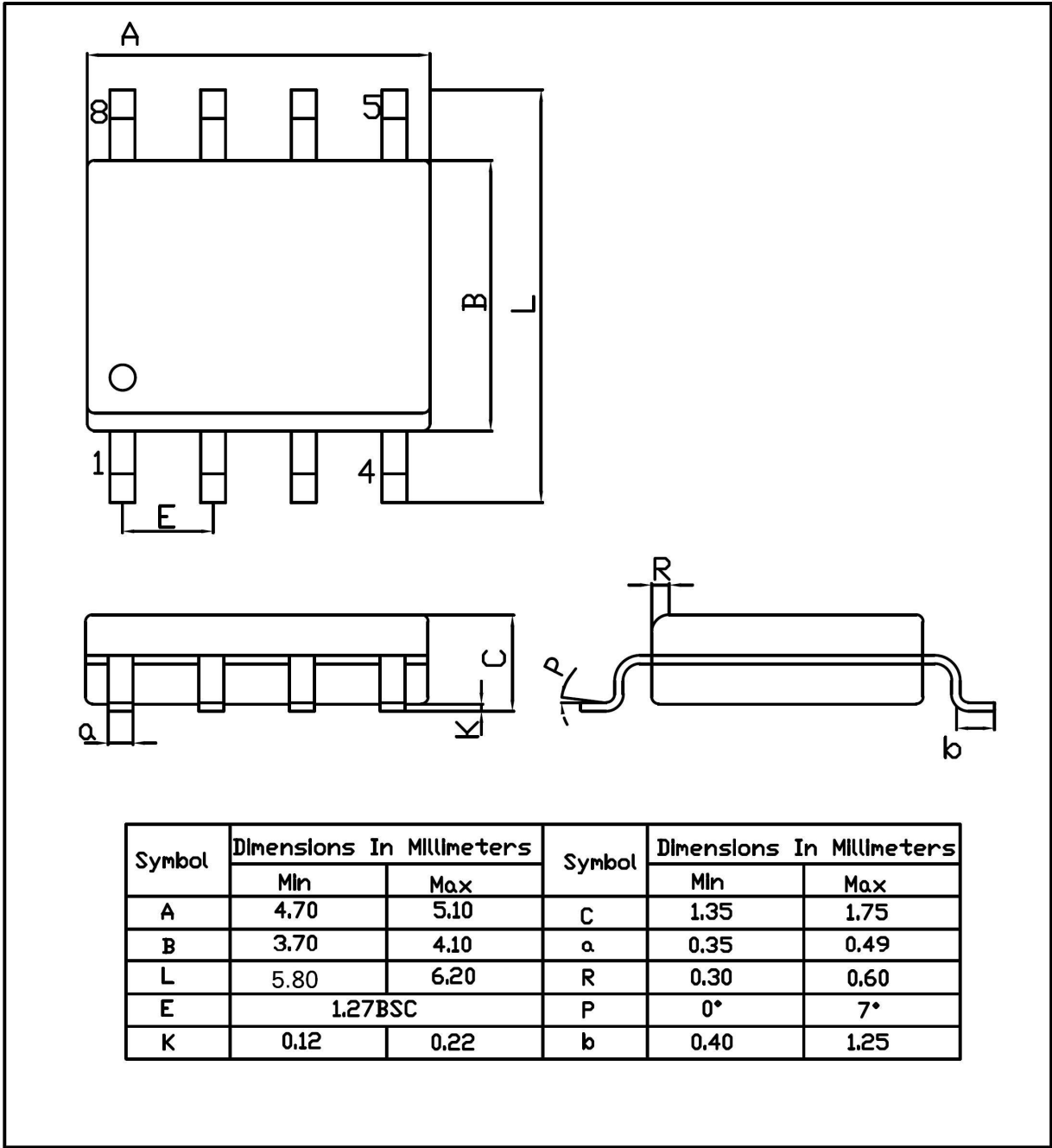
电参数曲线图 / Electrical Characteristic Curve

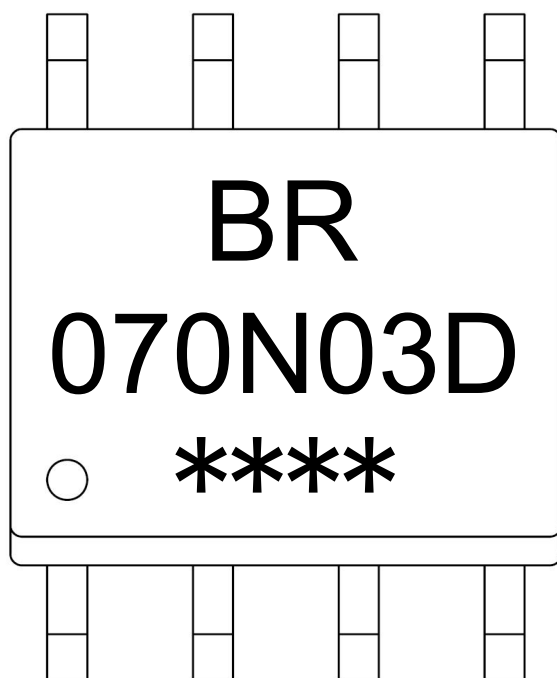


外形尺寸图 / Package Dimensions

SOP-8

Unit:mm



**印章说明 / Marking Instructions**

说明：

BR： 为公司代码

070N03D： 为型号代码

****： 为生产批号代码，随生产批号变化

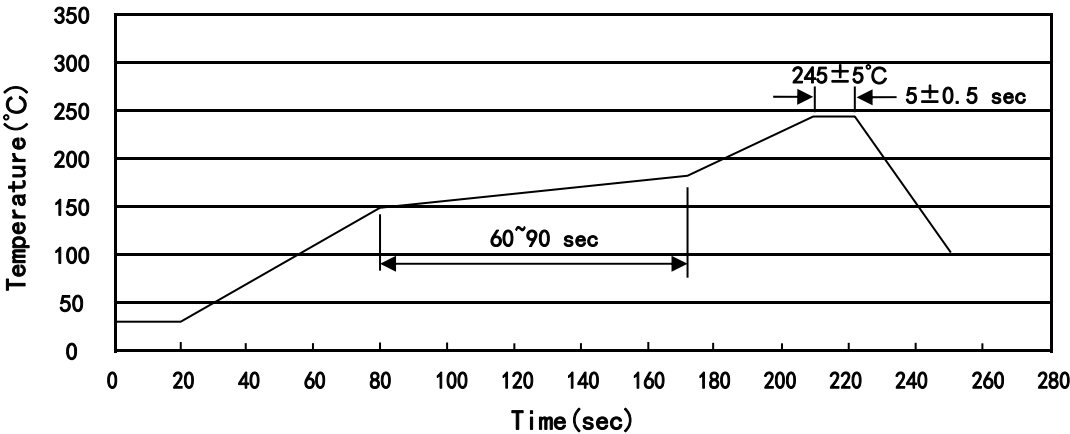
Note:

BR: Company Code

070N03D: Product Type

****: Lot No. Code, code change with Lot No

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150~180℃，时间 60~90sec;
- 2、峰值温度 245±5℃，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10℃/sec.

Note:

- 1.Preheating:150~180℃, Time:60~90sec.
- 2.Peak Temp.:245±5℃, Duration:5±0.5sec.
3. Cooling Speed: 2~10℃/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5℃ 时间：10±1 sec. Temp.:260±5℃ Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOP/ESOP-8	4,000	2	8,000	6	48,000	13" ×12	360×360×50	380×335×366

使用说明 / Notices